Plasma-Assisted Etching and Reactive Ion Etching Using High and Low Density Plasmas

Event - Plasma-Assisted Etching and Reactive Ion Etching Using High and Low Density Plasmas ↻

Title	Plasma-Assisted Etching and Reactive Ion Etching Using High and Low Density Plasmas
When	Mo, 24. Oktober 2016 - Di, 25. Oktober 2016

Description

Plasma-Assisted Etching and Reactive Ion Etching Using High and Low Density Plasmas

TECHNOLOGY FOCUS OF THIS COURSE
Plasma-assisted etching is used in many technologies. It is most critical in ultra large scale integrated (ULSI) circuit fabrication and is used many times during the processing of a single wafer. Other areas that rely heavily on plasma-assisted etching include micro-electrical-mechanical (MEMS) structure fabrication, many so-called nano-science processes, micro-optical and photonic activities and numerous other material processing where near room temperature chemical reactions are required.

COURSE OBJECTIVES
The objective of this course is to describe the extent to which the fundamental processes in plasma-assisted etching are understood and to relate this understanding to the practical applications of the technology. The reactive gas plasma environment is very complex and depends strongly on the type of plasma source that is used.

Atoms, molecular radicals and energetic positive ions dominate the etching surface chemistry. The fundamental aspects of the reactions of these species with solid surfaces have been studied extensively and a qualitative understanding of this complex surface chemistry has been developed.

Please learn more about this event by following link:
http://www.cei.se/find-your-course/semiconductor-technology/electronic-and-photonic-devices/c87-plasma-assisted-etching-and-reactive-ion-etching-using-high-and-low-density-plasmas.aspx

Venue - Grenoble

Location	Grenoble
City	Grenoble
Country	FR